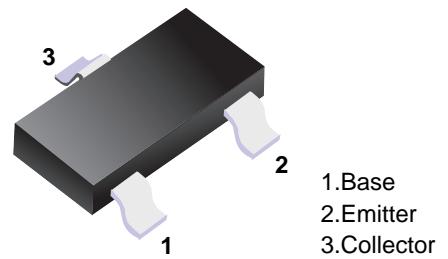


## MMBT2222A

### ■ NPN Transistors



#### ■ Features

- Epitaxial planar die construction.
- Complementary PNP type available(MMBT2907A)

#### ■ Simplified outline(SOT-23)

#### ■ Marking

Marking	1P
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#### ■ Absolute Maximum Ratings Ta = 25°C

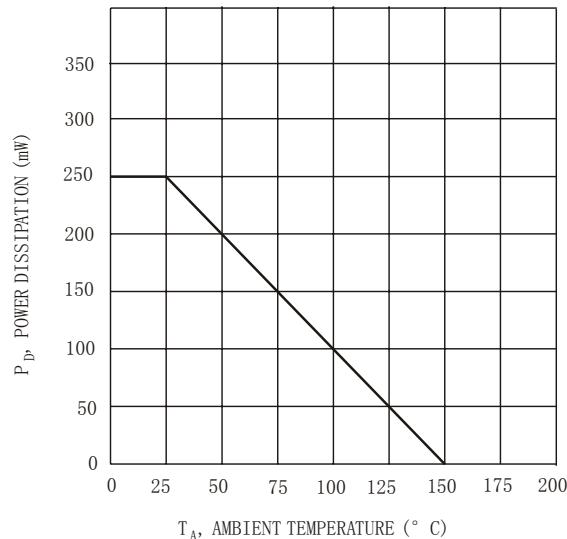
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CBO</sub>	70	
Collector - Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter - Base Voltage	V <sub>EBO</sub>	6	
Collector Current - Continuous	I <sub>c</sub>	600	mA
Power Dissipation	P <sub>D</sub>	250	mW
Thermal resistance from junction to ambient	R <sub>θJA</sub>	417	°C/W
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = 100 μA, I <sub>E</sub> = 0	75			V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = 10 mA, I <sub>B</sub> = 0	40			V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100 μA, I <sub>c</sub> = 0	6			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			100	nA
Collector cut-off current	I <sub>CEx</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =-3V			10	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>c</sub> =0			100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> = 0.1mA	40			
		V <sub>CE</sub> =10V, I <sub>c</sub> = 150mA	100		300	
		V <sub>CE</sub> =10V, I <sub>c</sub> = 500mA	42			
collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> = 150 mA; I <sub>B</sub> = 15 mA			0.3	V
		I <sub>c</sub> = 500 mA; I <sub>B</sub> = 50 mA			1	V
base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> = 150 mA; I <sub>B</sub> = 15 mA	0.6		1.2	V
		I <sub>c</sub> = 500 mA; I <sub>B</sub> = 50 mA			2	V
Transition frequency	f <sub>T</sub>	I <sub>c</sub> = 20 mA; V <sub>CE</sub> = 20 V; f = 100 MHz	300			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-0.5V, I <sub>c</sub> =150mA, I <sub>B1</sub> = 15mA			10	ns
Rise time	t <sub>r</sub>				25	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>c</sub> =150mA, I <sub>B1</sub> =-I <sub>B2</sub> =15mA			225	ns
Fall time	t <sub>f</sub>				60	ns

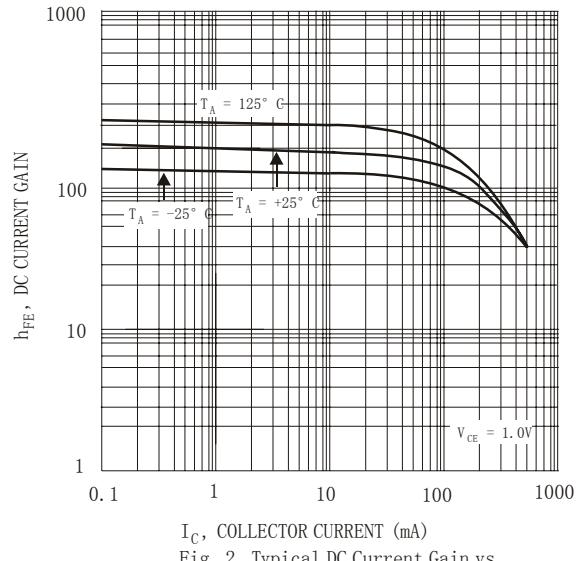
\* pulse test: Pulse Width ≤300μs, Duty Cycle≤ 2.0%.

■ Typical Characteristics



$T_A$ , AMBIENT TEMPERATURE (° C)

Fig. 1, Max Power Dissipation vs  
Ambient Temperature



$I_C$ , COLLECTOR CURRENT (mA)

Fig. 2, Typical DC Current Gain vs  
Collector Current

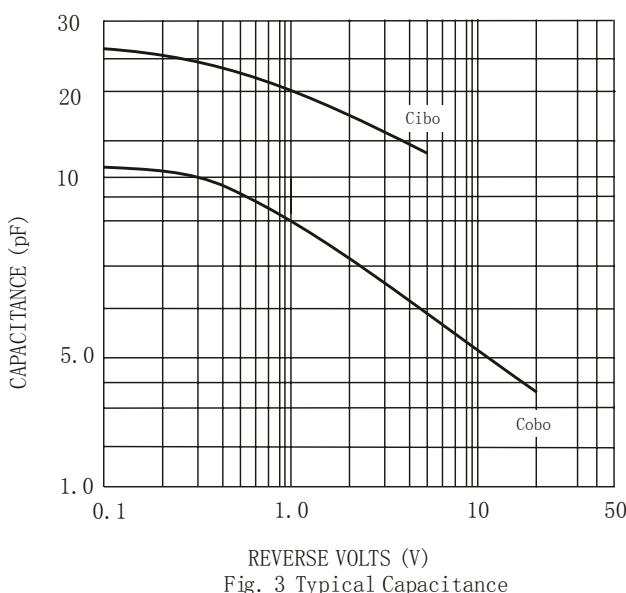
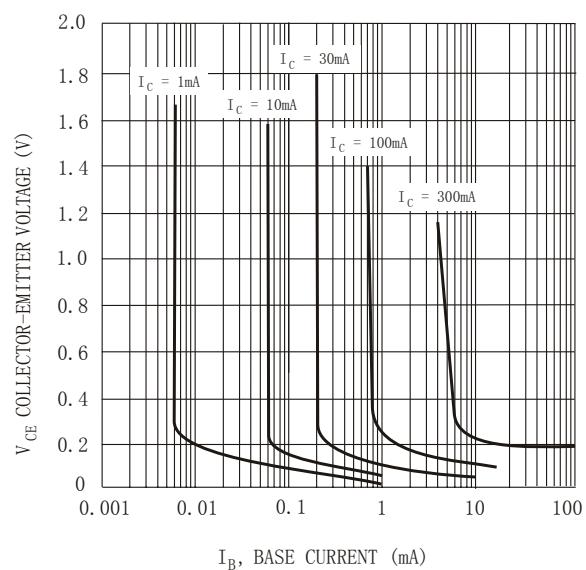


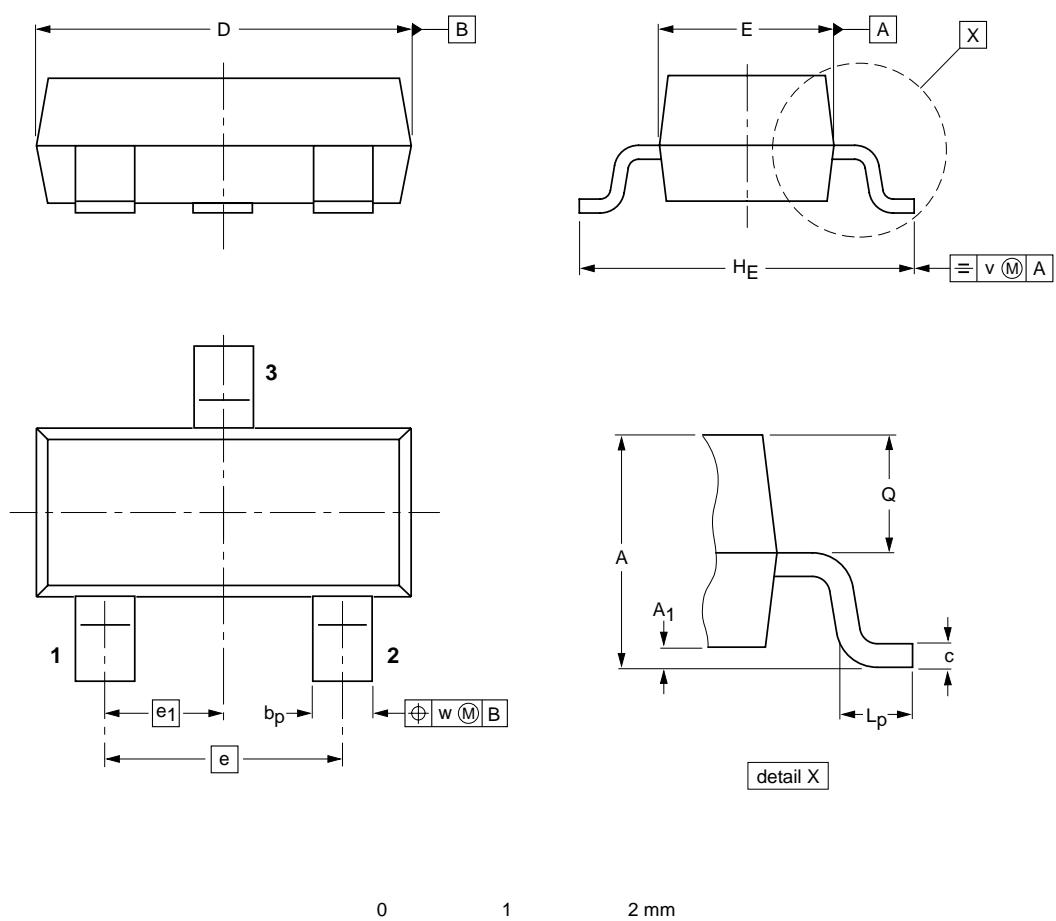
Fig. 3 Typical Capacitance



$I_B$ , BASE CURRENT (mA)

Fig. 4 Typical Collector Saturation Region

■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	$A_1$ max.	$b_p$	c	D	E	e	$e_1$	$H_E$	$L_p$	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1